

## DIO7330

5.5V rated 2.4A capable slew rate controlled load switch

#### Features

- 1.8V to 5.5V operation voltage range
- Low quiescent current < 1µA when disabled</li>
- Reverse current blocking when switch is off
- 40mΩ N-MOSFET
- DC Current Up to 2.4A
- Peak Current Up to 5A
- Built-in Soft-Start 3ms
- Active High with Integrated Bridge
- Pb-Free Device DFN-4 1.2x1.6mm

#### Applications

- Cell Phone and Digital Camera
- PDA and Notebook
- LCD Monitor
- TV and Set-Top Box

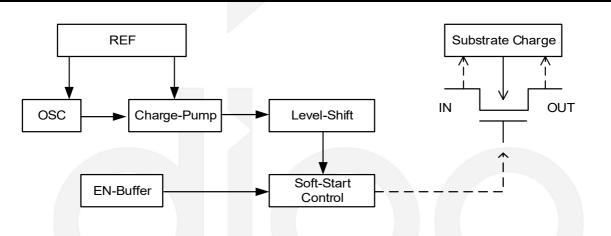
## **Block Diagram**

#### **Descriptions**

The DIO7330 is a Low On-Resistance N-channel MOSFET controlled by a soft-start sequence of 3ms for mobile applications.

The low  $R_{DS}(on)$  allows system supplying or battery charging up to DC 2.4A.The device is enable automatically if a power supply is connected on  $V_{IN}$  pin (active High) and maintained off if no power input(internal pull down).

Due to the current consumption optimization, the leakage current is drastically decreased from the battery connected to the device, which allows extending the battery life.



## **Ordering Information**

Order Part Number	Top Marking		T <sub>A</sub>	Package		
DIO7330DN4	YW30	Green	-40 to +85°C	TDFN-4	Tape & Reel, 3000	



# **Pin Assignments**

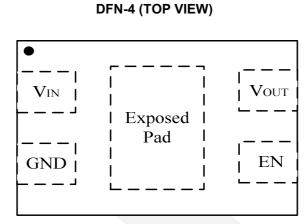


Figure 1 Pin Assignment

## **Pin Description**

Pin	Name	Туре	Description
1	V <sub>IN</sub>	Power	Switch Input voltage; connect a $1\mu$ F or greater ceramic capacitor from IN to GND as close as possible to the IC.
2	GND	Power	GND
3	EN	Input	Enable input, logic high active.
4	V <sub>out</sub>	Output	Switch Output; connect a $1\mu F$ capacitor from $V_{\text{OUT}}$ to GND as close as possible to the IC.
	Exposed Pad	Power	Exposed pad can be connected to GND plane for dissipation purpose or any other thermal plane.



### **Absolute Maximum Ratings**

Stresses beyond those listed under "Absolute Maximum Rating" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other condition beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maxim rating conditions for extended periods may affect device reliability.

Parameter		Rating	Unit	
V <sub>IN</sub>		-0.3 to 6	V	
V <sub>OUT</sub> ,EN		-0.3 to 6	V	
Storage Temperature		-65 to 150	°C	
Maximum Junction Range		-40 to 145	°C	
Thermal Resistance, θ <sub>JA</sub>		170	°C/W	
Power Dissipation, (T <sub>A</sub> =25°C)		580	mW	
Latch Up Protection		200	mA	
ESD	HBM, JEDEC: JESD22-A114	6		
	CDM, JEDEC : JESD22-C101	2	kV	

## **Recommended Operating Conditions**

The Recommended Operating Conditions table defines the conditions for actual device operation to ensure optimal performance to the datasheet specifications. DIOO does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V <sub>IN</sub>	Operational Power Supply		1.8		5.5	V
V <sub>EN</sub>	Enable Voltage		0		5.5	V
C <sub>IN</sub>	Decoupling input capacitor		1			μF
C <sub>OUT</sub>	Decoupling output capacitor	USB port per Hub	1			μF
Ι <sub>ουτ</sub>	Maximum DC Current	T <sub>A</sub> =25°C			3	А
I <sub>PEAK</sub>	Maximum Peak Current	1ms pulse width at 217Hz ,T <sub>A</sub> =25°C			5	А
T <sub>A</sub>	Ambient Temperature Range		-40	25	85	°C
TJ	Junction Temperature Range		-40	25	125	°C



### **Electrical Characteristics**

 $T_{\text{A}}\text{=}25^{\circ}\text{C}$   $V_{\text{IN}}$  = 5V, unless otherwise noted.

Symbol	Parameter	Conditions		Min.	Тур.	Max.	Unit		
POWER SWITCH									
R <sub>DS(ON)</sub>	Static drain-source on-state resistance	V <sub>IN</sub> =1.8~5.5V,T <sub>A</sub> = 25°C			40		mΩ		
		I <sub>OUT</sub> =200mA,-40°C< T <sub>A</sub> <85°C				70	mΩ		
t <sub>R</sub>	Switch turn-on edge rising time	V <sub>IN</sub> =4.5V	$C_{LOAD}$ =100µF, $R_{LOAD}$ =150 $\Omega$	2	2.5	5	ms		
t⊨	Switch turn-off edge falling time	V <sub>IN</sub> =4.5V C <sub>LOAD</sub> =100μF,R <sub>LOAD</sub> =150Ω			3		ms		
t <sub>DON</sub>	Switch turn-on delay	V <sub>IN</sub> =4.5V; C <sub>LOAD</sub> =100µF	50% of EN pin to $V_{OUT}$ =10% of fully on		1.5		ms		
t <sub>DOFF</sub>	switch turn-off delay				10		μs		
	NPUT EN								
VIH	High-level input voltage			1.45			V		
VIL	Low-level input voltage					0.85	V		
R <sub>PD</sub>	Pull-down resistance at EN pin	$T_A = -45^{\circ}C$ to +85°C			1		MΩ		
REVERSE	REVERSE-LEAKAGE PROTECTION								
I <sub>REV</sub>	Reverse-current protection	V <sub>IN</sub> =0V, V <sub>OUT</sub> =4.2V, -40°C< T <sub>A</sub> <85°C, EN="0"			1	2	μA		
QUIESCENT CURRENT									
Ι <sub>Q</sub>	Current consumption	V <sub>IN</sub> =5V, V <sub>OUT</sub> floating, EN =5V			100	180	μA		
I <sub>SDN</sub>	shutdown current	V <sub>IN</sub> =5V, En="0", V <sub>OUT</sub> =GND, -40°C< T <sub>A</sub> <85°C				1	μA		

Note: This parameter is guaranteed by design and characterization.



#### **Application information**

#### Enable

Enable pin voltage in the active high means on. This part is automatically turned on when the input voltage enables the device. In the other side, this part is turned off when the input voltage is not available, which limits current consumption from battery to  $V_{OUT}$  pin.

#### Input Capacitor

To limit the voltage drop on the input supply caused by transient inrush currents, an input capacitor is placed to the  $V_{IN}$  and GND as close as possible. The value of the input capacitor is recommended 1µF at least. Higher values capacitor can help to further reduce the voltage drop.

#### **Output Capacitor**

While the device works, a capacitor from 100nF to  $1\mu$ F across V<sub>OUT</sub> and GND is recommended to accommodate load transient condition. It also helps to prevent parasitic inductance forces V<sub>OUT</sub> below GND when switching off. Output capacitor has the minimal effect on device's turn on slew rate time.

#### **Blocking Control**

The blocking control circuitry switches the bulk of the power NMOS. When the part is off (No  $V_{IN}$  or EN tied to GND externally), the body diode limits the leakage current  $I_{REV}$  from OUT to IN. In this condition, the anode of the body diode is connected to IN pin and the cathode is connected to OUT pin. During the operation, the anode of the body diode is connected to OUT pin and the cathode is connected to IN pin to prevent the discharge of the power supply.



## CONTACT US

Dioo is a professional design and sales corporation for high-quality and performance analog semiconductors. The company focuses on industry markets, such as, cell phone, handheld products, laptop, and medical equipment and so on. Dioo's product families include analog signal processing and amplifying, LED drivers and charger IC. Go to <a href="http://www.dioo.com">http://www.dioo.com</a> for a complete list of Dioo product families.

For additional product information, or full datasheet, please contact with our Sales Department or Representatives.

#### **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Power Switch ICs - Power Distribution category:

Click to view products by Dioo manufacturer:

Other Similar products are found below :

TCK111G,LF(S FPF1018 DS1222 TCK2065G,LF SZNCP3712ASNT3G MIC2033-05BYMT-T5 MIC2033-12AYMT-T5 MIC2033-05BYM6-T5 SLG5NT1437VTR SZNCP3712ASNT1G NCV330MUTBG DML1008LDS-7 KTS1670EDA-TR KTS1640QGDV-TR KTS1641QGDV-TR NCV459MNWTBG FPF2260ATMX U6513A U6119S NCP45780IMN24RTWG MAX14919ATP+ MC33882PEP TPS2021IDRQ1 TPS2104DBVR MIC2098-1YMT-TR MIC94062YMT TR MP6231DN-LF MIC2075-2YM MIC2095-2YMT-TR MIC94068YML-TR SIP32461DB-T2-GE1 NCP335FCT2G TCK105G,LF(S AP2151DSG-13 MIC94094YC6-TR MIC94064YC6-TR MIC2505-1YM MIC94042YFL-TR MIC94041YFL-TR MIC2005-1.2YM6-TR TPS2032QDRQ1 SIP32510DT-T1-GE3 NCP333FCT2G NCP331SNT1G TPS2092DR TPS2063DR TPS2042P MIC2008YML-TR MIC2040-1YMM TPS22810DRVR